

2N7002P,215 Datasheet



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DiGi Electronics Part Number 2N7002P,215-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number 2N7002P,215

Description MOSFET N-CH 60V 360MA TO236AB

Detailed Description N-Channel 60 V 360mA (Ta) 350mW (Ta) Surface M

ount TO-236AB



Tel: +00 852-30501935

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Manufacturer Product Number:	Manufacturer:
2N7002P,215	Nexperia USA Inc.
Series:	Product Status:
	Not For New Designs
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	360mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	1.60hm @ 500mA, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.4V @ 250μA	0.8 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	50 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	350mW (Ta)
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
2N7002	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



2N7002P

60 V, 360 mA N-channel Trench MOSFET

23 November 2020

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- · Very fast switching
- · Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	360	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 500 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.01; T_j = 25 °C		-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 360 mA N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D
2	S	source		
3	D	drain		G LETA
			1 2	mbb076 S
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
2N7002P		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002P	LW%

[1] % = placeholder for manufacturing site code

60 V, 360 mA N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	360	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	280	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.2	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	420	mW
		T _{sp} = 25 °C		-	1140	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	'		•
Is	source current	T _{amb} = 25 °C	[1]	-	360	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

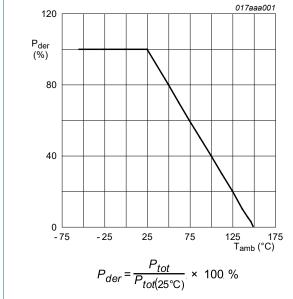


Fig. 1. Normalized total power dissipation as a function of ambient temperature

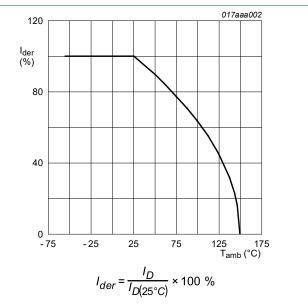


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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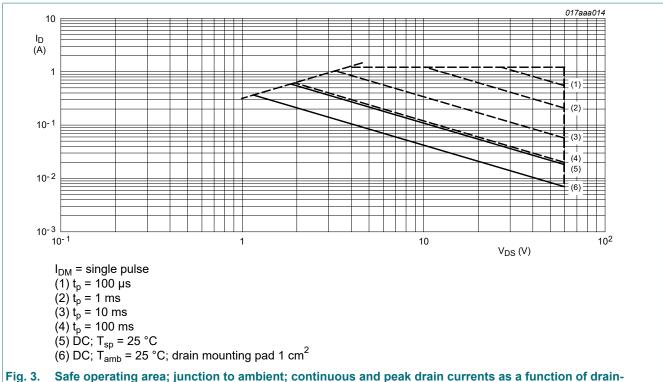


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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60 V, 360 mA N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	310	370	K/W
jun	junction to ambient		[2]	-	260	300	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

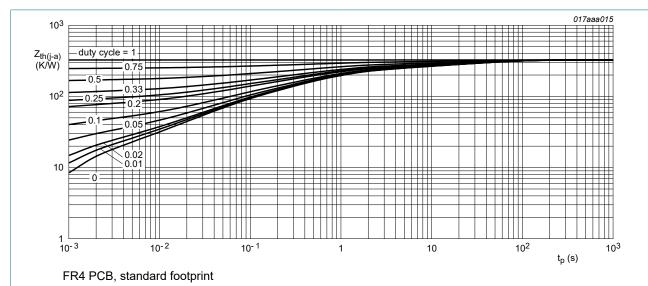


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

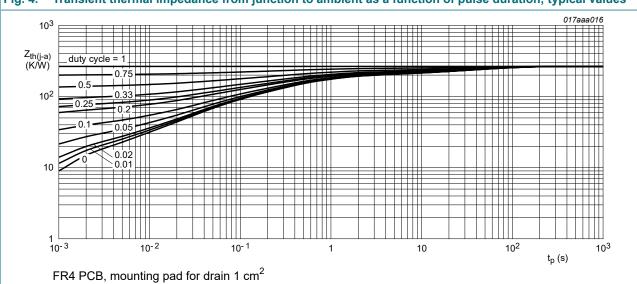


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 360 mA N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.75	2.4	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
DOON	drain-source on-state resistance	V_{GS} = 5 V; I_{D} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	1.3	2	Ω
		V_{GS} = 10 V; I_D = 500 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.01; T_j = 25 °C	-	1	1.6	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.01; T_{j} = 25 °C	-	400	-	mS
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 300 mA; V _{GS} = 4.5 V;	-	0.6	0.8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	30	50	pF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	3	6	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time] [-	10	20	ns
t _f	fall time]	-	5	-	ns
Source-drai	in diode	·				
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

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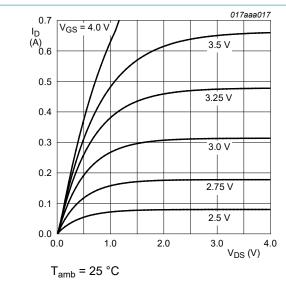
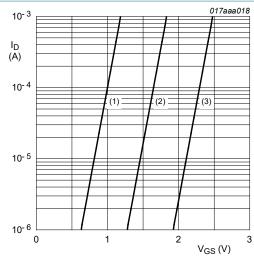


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

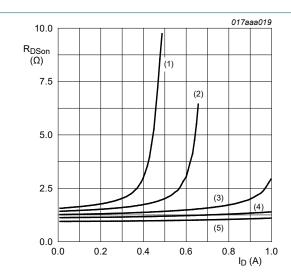


 T_{amb} = 25 °C; V_{DS} = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 T_{amb} = 25 °C

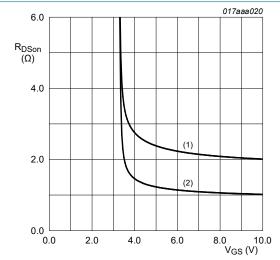
(1) $V_{GS} = 3.25 \text{ V}$

 $(2) V_{GS} = 3.5 V$

(3) $V_{GS} = 4 V$ (4) $V_{GS} = 5 V$

 $(5) V_{GS} = 10 V$





 $I_D = 500 \text{ mA}$

(1) T_{amb} = 150 °C

 $(2) T_{amb} = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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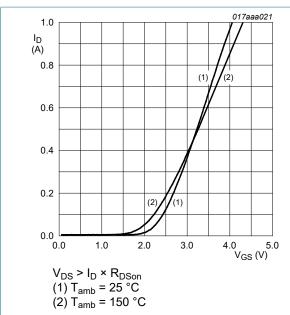


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

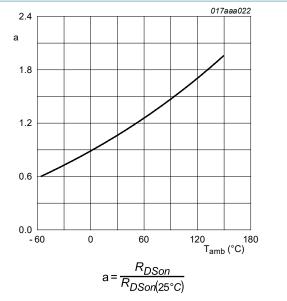
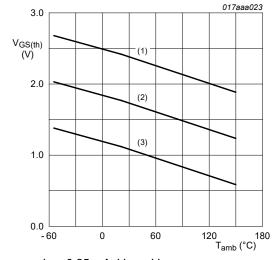


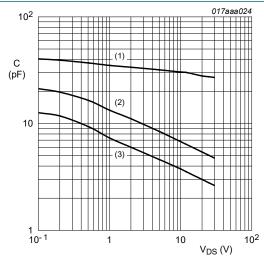
Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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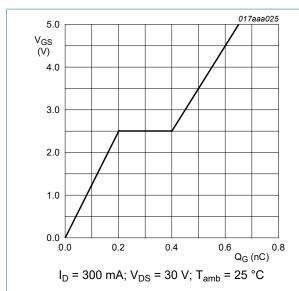


Fig. 14. Gate-source voltage as a function of gate charge; typical values

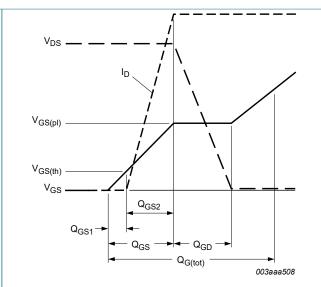
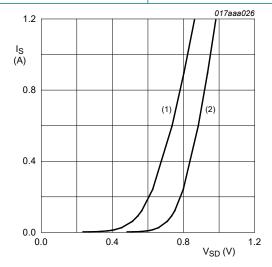


Fig. 15. Gate charge waveform definitions

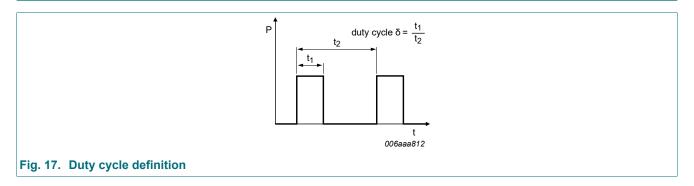


V_{GS} = 0 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

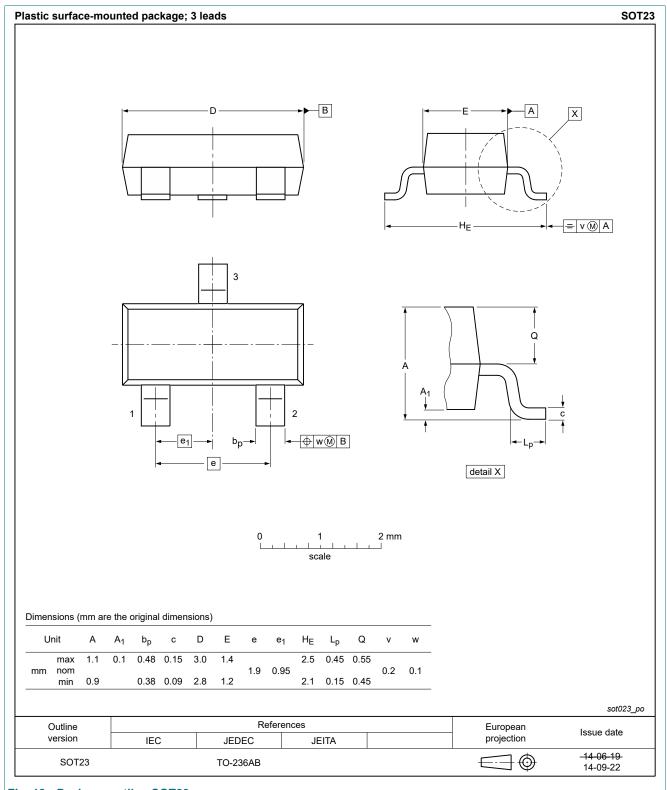
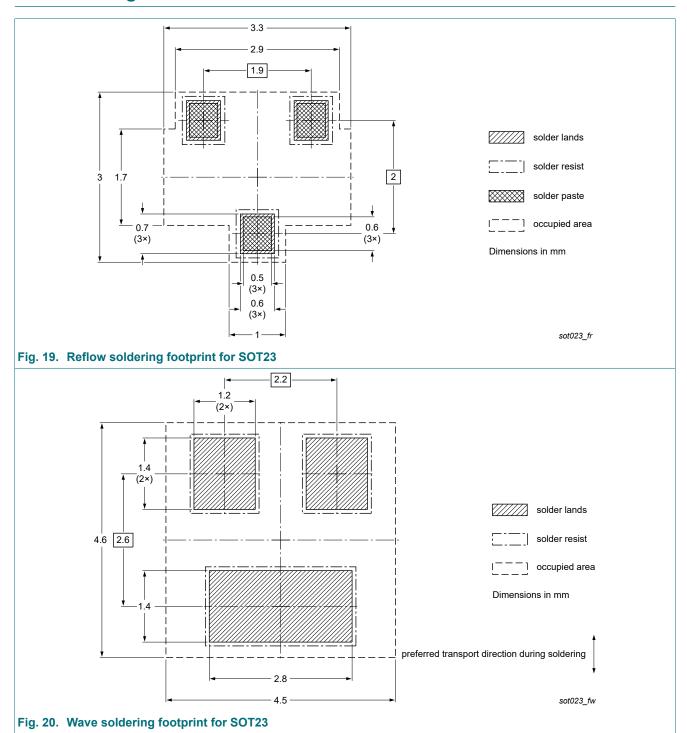


Fig. 18. Package outline SOT23

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
2N7002P v.3	20201123	Product data sheet	-	2N7002P v.2	
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Chapter "Characteristics": Typo correction for I_{GSS}. 				
2N7002P v.2	20100729	Product data sheet	-	2N7002P v.1	
2N7002P v.1	20100419	Product data sheet	-	-	

60 V, 360 mA N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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